

Title (en)

SEMICONDUCTOR LIGHT-EMITTING DEVICE AND METHOD FOR MAKING SAME

Title (de)

LICHTEMITTIERENDES HALBLEITERBAUELEMENT UND VERFAHREN ZU SEINER HERSTELLUNG

Title (fr)

DISPOSITIF ELECTROLUMINESCENT A SEMI-CONDUCTEUR ET SON PROCEDE DE FABRICATION

Publication

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Application

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Abstract (en)

[origin: WO2007036164A1] One embodiment of the present invention provides a semiconductor light-emitting device, which comprises: an upper cladding layer; a lower cladding layer; an active layer between the upper and lower cladding layers; an upper ohmic-contact layer forming a conductive path to the upper cladding layer; and a lower ohmic-contact layer forming a conductive path the lower cladding layer. The lower ohmic-contact layer has a shape substantially different from the shape of the upper ohmic-contact layer, thereby diverting a carrier flow away from a portion of the active layer which is substantially below the upper ohmic-contact layer when a voltage is applied to the upper and lower ohmic-contact layers.

IPC 8 full level

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